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| Objective |
| Batch name: Process template |
| This process flows is a guideline on how to spin, develop and rinse CSAR6100 on non-conducting substrates such as SiO2 and quartz.  |

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| Step Heading | Equipment |  | Comments |
| 1. Pretreatment
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| * 1. Surface treatment
 | BHF dip *or*HMDS | BHF dip for Si substrates (30 sec, H2O 5 min) HMDS treatment for SiO2 and III-V substrates | Generally, pre-treatment is not recommended.  |
| 1. Spin coat of CSAR
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| * 1. Coat wafers
 | Spin Coater | **Resist:** CSAR 6200**Spin:** 60 sec @ 4000 rpm (~180 nm)**Softbake:** 1 min @ 150 °C (hotplate) | Use syringe with filter or disposable pipette (cleaned by N2 gun). Softbake is not a crucial step according to AllResist |
| 1. Coat with Thermal Aluminum (only for non-conductive substrates)
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| * 1. Coat with Al
 | Wordentec | Thickness: 20 nmRate: 15 Å/S |  |
| 1. E-beam exposure
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| * 1. E-beam exposure
 | E-beam writer | Dose: 200 - 350 µC/cm2; a dose-test is required. See e-beam logbook for inspiration. | Dose depends strongly on substrate material, thickness of resist, critical dimension and load of pattern. |
| 1. Removal of Thermal Aluminum
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| * 1. Removal of Al
 | Developer: TMAH Manual | Recipe: SP 60sRinse in H2O, 1-2 minBlow dry with N2 or spin dry.The etch rate of Al in ‘Developer: TMAH Manual’ is approximately 0.5 nm/s. For Al layers thinner than 20 nm, a 30s single puddle recipe should be enough. |  |
| 1. Development & Rinse
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| * 1. Develop-ment
 | Beaker, fumehood in D-4 | Develop with AR 600-546, 60 secRinse in IPA, 60 secblow dry with N2 |  |
| 1. Lift-off and Strip
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| * 1. Lift-off
 | Beaker, fumehood in D-4 | Remover AR 600-71 | USE REMOVER AR 600-71 ONLY AT ROOM TEMPERATURE |